BTA440J-800BT

3Q Hi-Com Triac

Rev.01 - 20 December 2024 Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a TO3PF package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series BT" triac will commutate the full RMS current at the maximum rated junction temperature ($T_{j(max)}$ = 150 °C) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required

2. Features and benefits

- High current TRIAC
- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability ($T_{j(max)}$ = 150 °C)
- High voltage capability
- Least sensitive gate for highest noise immunity
- Low thermal resistance
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Insulated tab rated at 2500Vrms

3. Applications

- Applications subject to high temperature ($T_{j(max)}$ = 150 °C)
- High current / high surge applications
- High power / industrial controls - e.g. heating, motors, lighting

4. Quick reference data

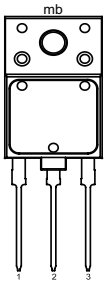
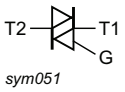
Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
V_{DRM}	repetitive peak off-state voltage			800			V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 79$ °C; Fig. 1; Fig. 2; Fig. 3		40			A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5		400			A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms		440			A
T_j	operating junction temperature			-40 to 150			°C
Symbol	**Parameter**	**Conditions**	**Notes**	**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	-	50	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	-	50	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	-	50	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	80	mA
V_T	on-state voltage	I_T = 56.6 A; T_j = 25 °C; Fig. 10		-	-	1.5	V

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		1000	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 20 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit		15	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA440J-800BT	TO3PF	BTA440J-800BTQ	Tube	30	SOT1293	01-Mar-2017

7. Marking

Table 4. Marking codes

Type number	Marking codes	
	Assembly factory: A	Assembly factory: d
BTA440J-800BT	BTA440J 800BT PJAxxxx xx	BTA440J 800BT PJdxxxx xx

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak off-state voltage			800	V
V_{RRM}	repetitive peak reverse voltage			800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 79$ °C; Fig 1; Fig 2; Fig 3		40	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig 4; Fig 5		400	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		440	A
I^2t	I^2t for fusing	$t_p = 10$ ms; SIN		800	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 100$ mA		150	A/µs
I_{GM}	peak gate current	$t_p = 20$ µs		8	A
P_{GM}	peak gate power	$t_p = 20$ µs		40	W
$P_{G(AV)}$	average gate power			1	W
T_{stg}	storage temperature			-40 to 150	°C
T_j	operating junction temperature			-40 to 150	°C

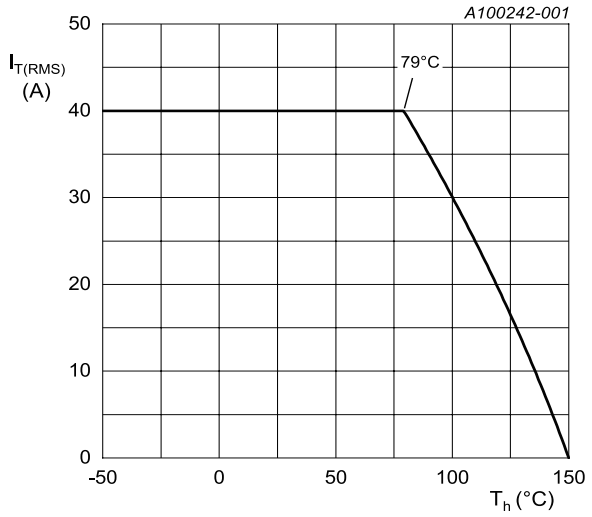
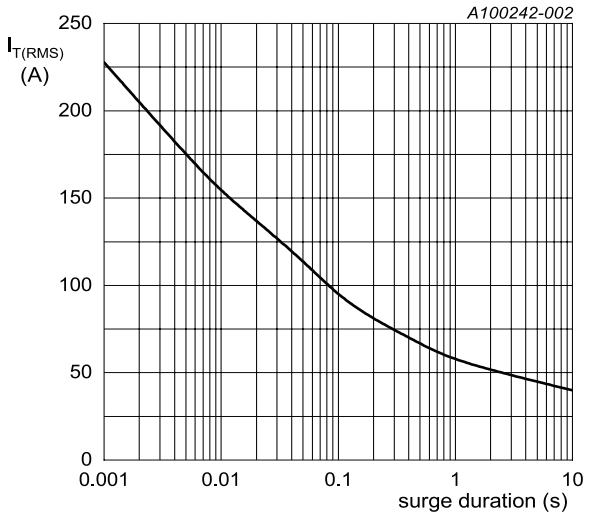
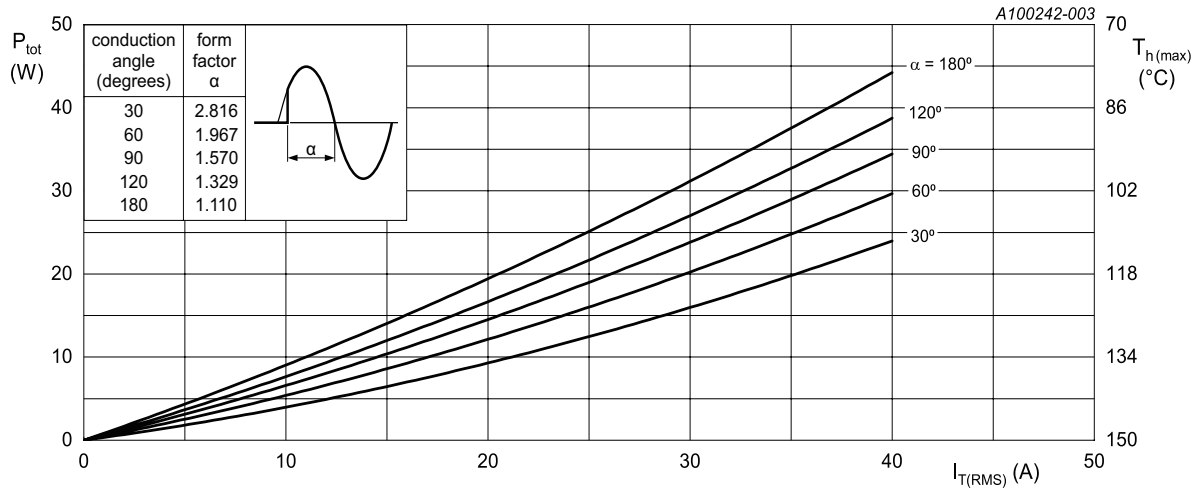


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values



f = 50 Hz; $T_h = 79$ °C

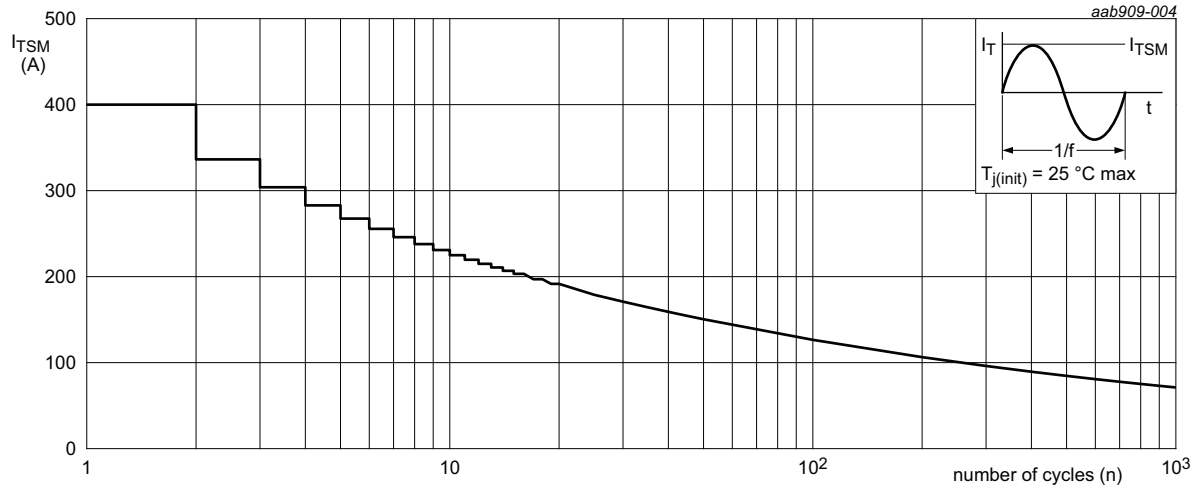
Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

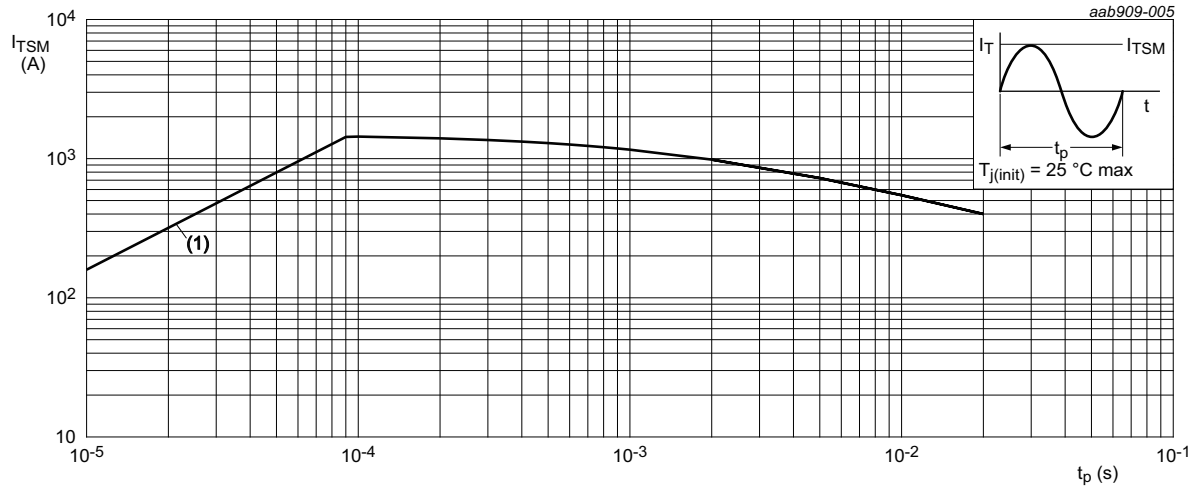
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20$ ms

(1) dI_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle; Fig. 6		-	-	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	35	-	K/W

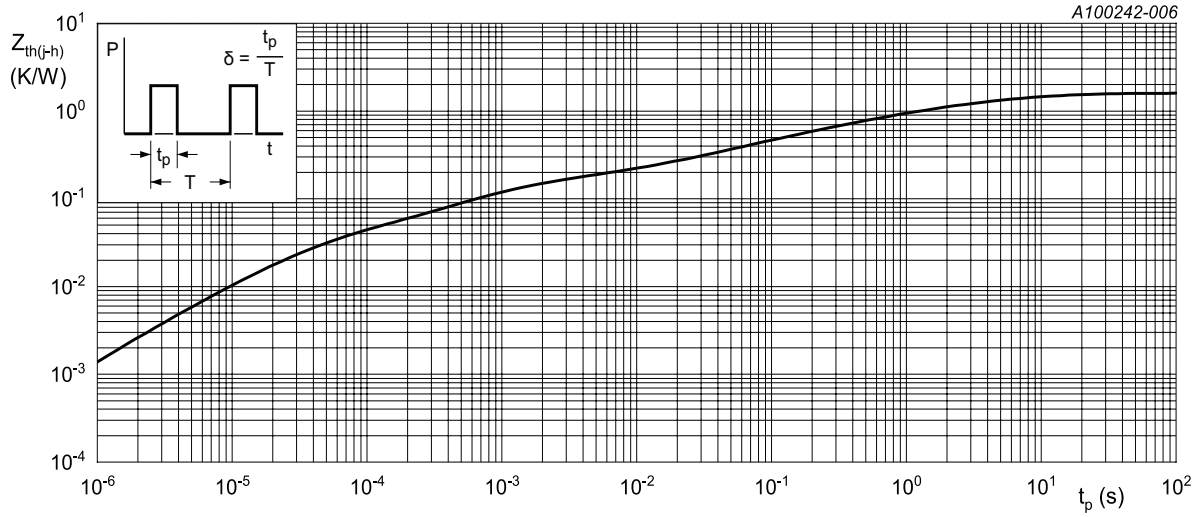


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

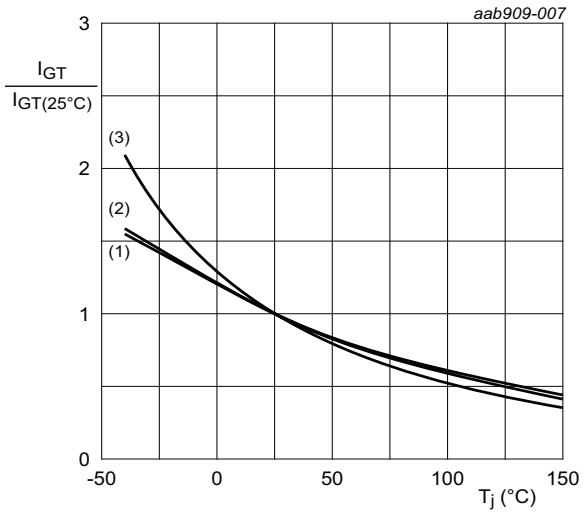
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; T_{mb} = 25 °C		-	-	2500	V

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	-	50	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	-	50	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	-	50	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 8		-	-	85	mA
		V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8		-	-	160	mA
		V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; Fig. 8		-	-	85	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	80	mA
V_T	on-state voltage	I_T = 56.6 A; T_j = 25 °C; Fig. 10		-	-	1.5	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	0.8	1.3	V
		V_D = 400 V; I_T = 0.1 A; T_j = 150 °C		0.20	0.45	-	V
I_D	off-state current	V_D = 800 V; T_j = 25 °C		-	-	10	µA
		V_D = 800 V; T_j = 150 °C		-	-	2	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		1000	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 20 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit		15	-	-	A/ms



(1) T2+ G+
(2) T2+ G-
(3) T2- G-

Fig. 7. Normalized gate trigger current as a function of junction temperature

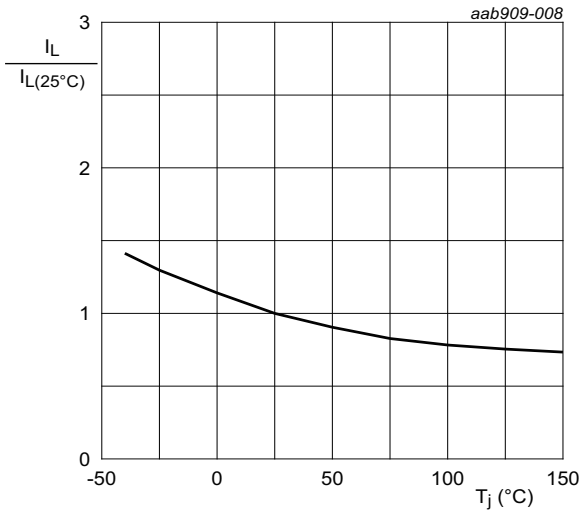


Fig. 8. Normalized latching current as a function of junction temperature

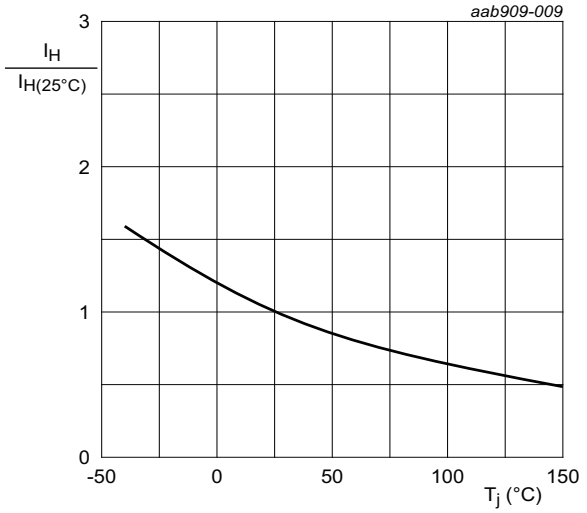
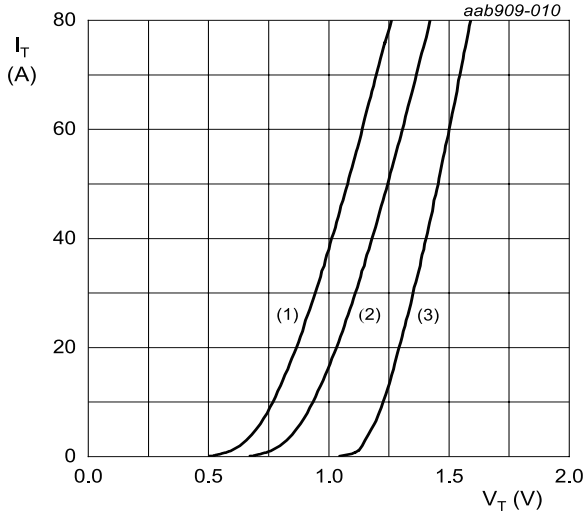


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 0.928 V; R_s = 0.0068 Ω
(1) T_j = 150 °C; typical values
(2) T_j = 150 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

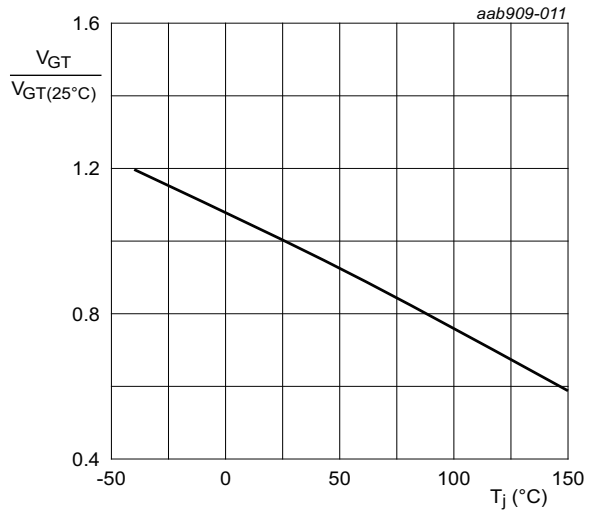
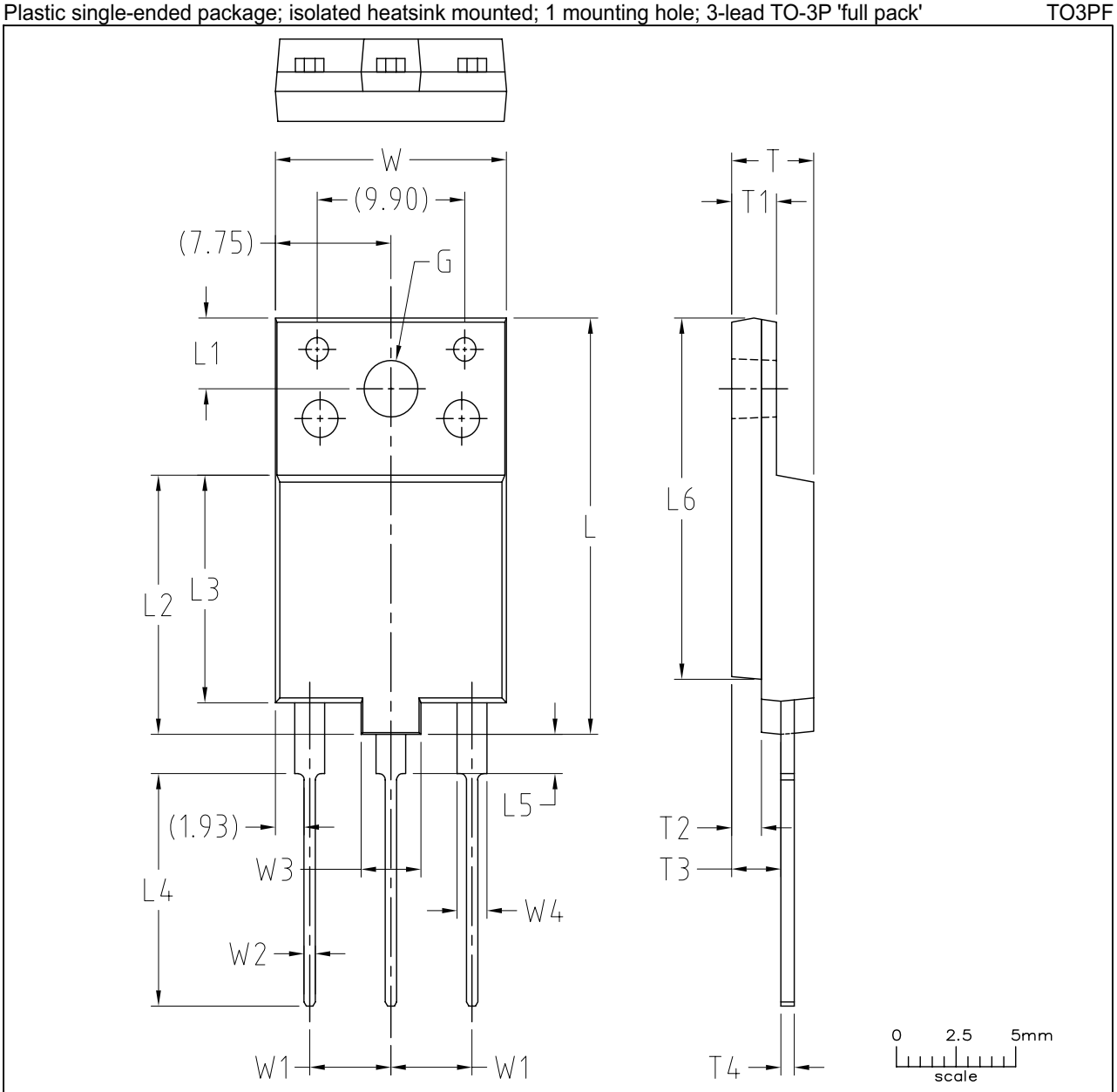


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack' TO3PF



RemarK : (X) the dimension X in blackets is for reference

UNIT	W	W1	W2	W3	W4	L	L1	L2	L3	L4	L5	L6	T	T1	T2	T3	T4	G(ø)
mm	15.7	5.75	0.95	4.20	2.20	26.7	4.6	16.7	14.7	15.0	2.7	23.2	5.7	3.2	2.2	3.5	1.1	3.8
	15.3	5.15	0.65	3.80	1.80	26.3	4.4	16.3	14.3	14.6	2.3	22.8	5.3	2.8	1.8	3.1	0.8	3.4

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
		TO−3PF				

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
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14. Contents

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